

# 1N17 ~ 1N19

## SCHOTTKY BARRIER RECTIFIERS

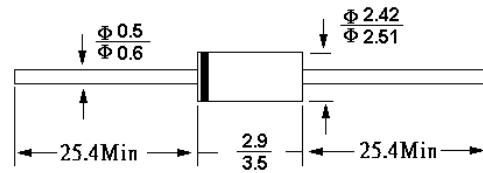
Reverse Voltage – 20 to 40 Volts

R-1

Forward current – 1.0 Amperes

### Features

- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability low forward voltage drop
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications



Dimensions in mm

### Mechanical data

- **Case:** R-1 molded plastic body
- **Terminals:** Plated axial leads, solderable per MIL-STD-750, method 2026
- **Polarity:** color band denotes cathode end
- **Mounting Position:** Any

## Absolute Maximum Ratings and Characteristics

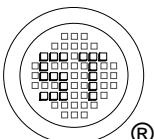
Ratings at 25°C ambient temperature unless otherwise specified.

	Symbols	1N17	1N18	1N19	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	20	30	40	Volts
Maximum RMS voltage	$V_{RMS}$	14	21	28	Volts
Maximum DC Blocking Voltage	$V_{DC}$	20	30	40	Volts
Maximum Non-repetitive Peak Reverse Voltage	$V_{RSM}$	24	36	48	Volts
Maximum Average Forward Rectified Current 0.375" (9.5mm) Lead Length At $T_L = 90^\circ\text{C}$	$I_{(AV)}$	1			Amps
Peak Forward Surge Current, 8.3ms Single half sine-wave Superimposed On Rated Load (JEDEC method) At $T_L = 70^\circ\text{C}$	$I_{FSM}$	25			Amps
Maximum Instantaneous Forward Voltage At 1 A	$V_F$	0.45	0.550	0.60	Volts
Maximum Instantaneous Forward Voltage At 3.1 A	$V_F$	0.75	0.875	0.90	Volts
Maximum Instantaneous Reverse Current at $T_A = 25^\circ\text{C}$ Rated DC Blocking Voltage $T_A = 100^\circ\text{C}$	$I_R$	0.5 10			mAmps
Typical Thermal Resistance	$R_{\theta JA}$ $R_{\theta JL}$	50 15			°C/W
Typical Junction Capacitance	$C_J$	110			pF
Storage and Operating Junction Temperature Range	$T_J, T_{Stg}$	-65 to +125			°C

Notes: 1. Pulse test: 300  $\mu\text{s}$  pulse width, 1% duty cycle

2. Thermal resistance (from junction to ambient) Vertical P.B.C. MOUNTED, 0.5" (12.7 mm) lead length

3. Measured at 1.0MHz and reverse voltage of 4.0 volts



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FIG.1-FORWARD CURRENT DERATING CURVE

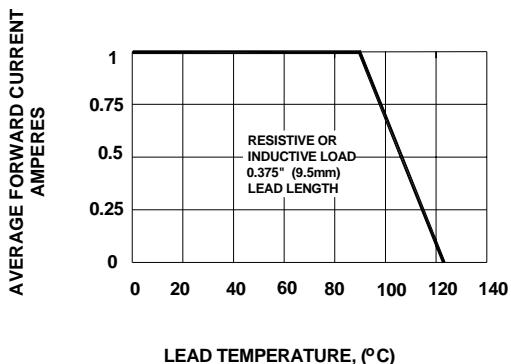


Fig.2- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

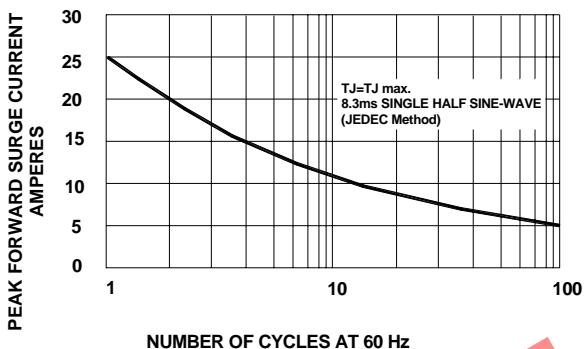


Fig.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

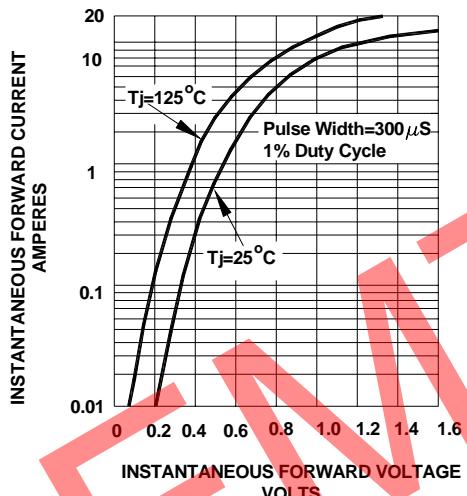


Fig.4- TYPICAL REVERSE CHARACTERISTICS

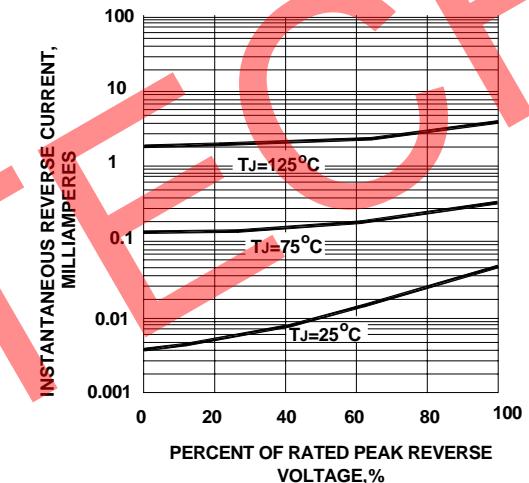


Fig.5- TYPICAL JUNCTION CAPACITANCE

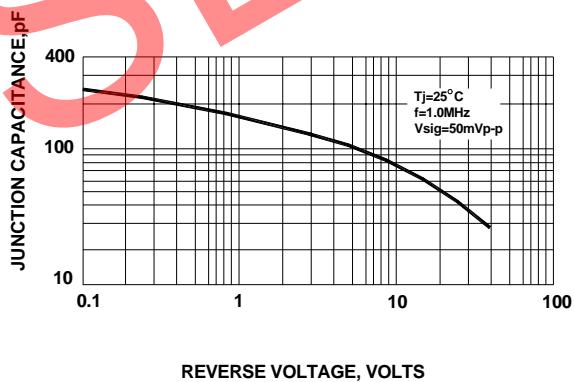
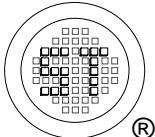
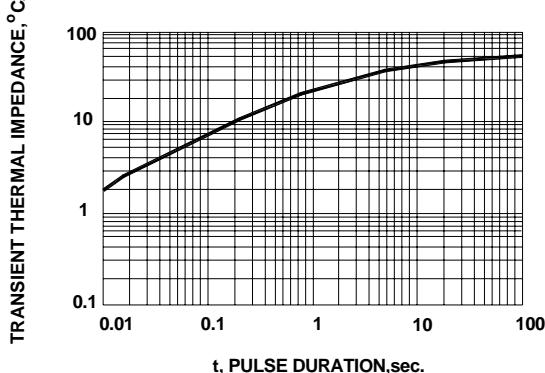
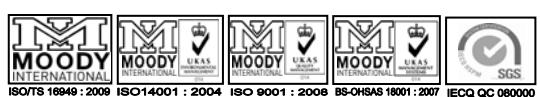


Fig.6- TYPICAL TRANSIENT THERMAL IMPEDANCE



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